2-Input NAND Schmitt-Trigger

The MC74VHC1G132 is a single gate CMOS Schmitt NAND trigger fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The MC74VHC1G132 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1G132 to be used to interface 5V circuits to 3V circuits.

The MC74VHC1G132 can be used to enhance noise immunity or to square up slowly changing waveforms.

- High Speed: $t_{PD} = 3.6 \text{ns}$ (Typ) at $V_{CC} = 5 \text{V}$
- Low Power Dissipation: $I_{CC} = 2\mu A$ (Max) at $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V

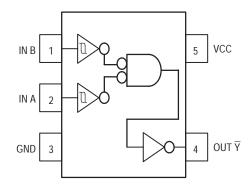


Figure 1. 5–Lead SOT–353 Pinout (Top View)

LOGIC SYMBOL





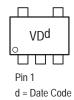
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SC-88A / SOT-353 DF SUFFIX CASE 419A

MARKING DIAGRAM



PIN ASSIGNMENT						
1	IN B					
2	IN A					
3	GND					
4	OUT Y					
5	VCC					

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

FUNCTION TABLE

Inp	uts	Output
Α	В	Ϋ́
L	L	Н
L	Н	Н
н	L	Н
Н	Н	L

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MAXIMUM RATINGS*

Characteristics	Symbol	Value	Unit
DC Supply Voltage	V _{CC}	-0.5 to +7.0	V
DC Input Voltage	VIN	-0.5 to +7.0	V
DC Output Voltage V _{CC} = 0 High or Low State	Vout	−0.5 to 7.0 −0.5 to V _{CC} + 0.5	V
Input Diode Current	Iк	-20	mA
Output Diode Current $(V_{OUT} < GND; V_{OUT} > V_{CC})$	IOK	+20	mA
DC Output Current, per Pin	IOUT	+25	mA
DC Supply Current, V_{CC} and GND	ICC	+50	mA
Power dissipation in still air, SC–88A †	PD	200	mW
Lead temperature, 1 mm from case for 10 s	ΤL	260	°C
Storage temperature	T _{stg}	-65 to +150	°C

* Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute–maximum–rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — SC--88A Package: -3 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	VCC	4.5	5.5	V
DC Input Voltage	VIN	0.0	5.5	V
DC Output Voltage	VOUT	0.0	VCC	V
Operating Temperature Range	TA	-55	+85	°C

			Vcc	т	A = 25°	0	T _A ≤	85°C	TA ≤ ′	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{T+}	Positive Threshold Voltage		3.0 4.5 5.5	1.50 2.35 2.80	1.88 2.66 3.21	2.25 3.10 3.70	1.50 2.35 2.80	2.25 3.10 3.70	1.50 2.35 2.80	2.25 3.10 3.70	V
V _T -	Negative Threshold Voltage		3.0 4.5 5.5	0.65 1.10 1.45	1.03 1.62 2.02	1.40 2.10 2.60	0.65 1.10 1.45	1.40 2.10 2.60	0.65 1.10 1.45	1.40 2.10 2.60	V
VH	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.85 1.05 1.20	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	0.30 0.40 0.50	1.60 2.00 2.25	V
VOH	Minimum High–Level Output Voltage I _{OH} = -50µA	VIN = VIH or VIL IOH = -50µA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		I _{OH} = -4mA I _{OH} = -8mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V _{OL}	Maximum Low–Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50µA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		I _{OL} = 4mA I _{OL} = 8mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	$V_{IN} = 5.5V \text{ or GND}$	0 to 5.5			±0.1		±1.0		±1.0	μA
ICC	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μA

DC ELECTRICAL CHARACTERISTICS

AC ELECTRICAL CHARACTERISTICS ($C_{load} = 50 \text{ pF}$, Input $t_{f}/t_{f} = 3.0 \text{ns}$)

Power Dissipation Capacitance (Note 1.)

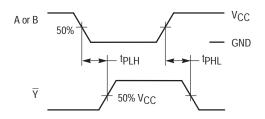
				Т	A = 25°0	C	TA ≤	85°C	T _A ≤ 125°C		
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
tplh, tphl	Maximum Propogation Delay, A	$V_{CC} = 3.3 \pm 0.3 V$	C _L = 15 pF C _L = 50 pF		4.6 6.1	11.9 15.4	1.0 1.0	14.0 17.5	1.0 1.0	16.1 19.6	ns
	or B to Y	$V_{CC} = 5.0 \pm 0.5 V$	C _L = 15 pF C _L = 50 pF		3.6 4.3	7.7 9.7	1.0 1.0	9.0 11.0	1.0 1.0	10.3 12.3	
C _{IN}	Maximum Input Capacitance				5.5	10		10		10	pF
	Typical @ 25°C, V _{CC} = 5.0V										

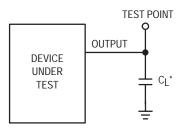
1. CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC}(OPR) = CPD \bullet V_{CC} \bullet f_{in} + I_{CC}$. CpD is used to determine the no–load dynamic power consumption; $P_D = CPD \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

pF

11

CPD





*Includes all probe and jig capacitance

Figure 3. Test Circuit

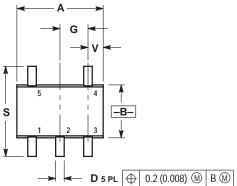
Figure 2. Switching Waveforms

DEVICE ORDERING INFORMATION

		-	Device Nome	nclature				
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type	Tape and Reel Size
MC74VHC1G132DFT1	MC	74	VHC1G	132	DF	T1	SC-88A / SOT-353	7–Inch/3000 Unit

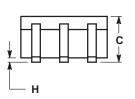
PACKAGE DIMENSIONS

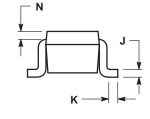


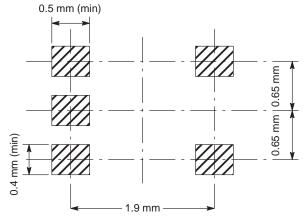


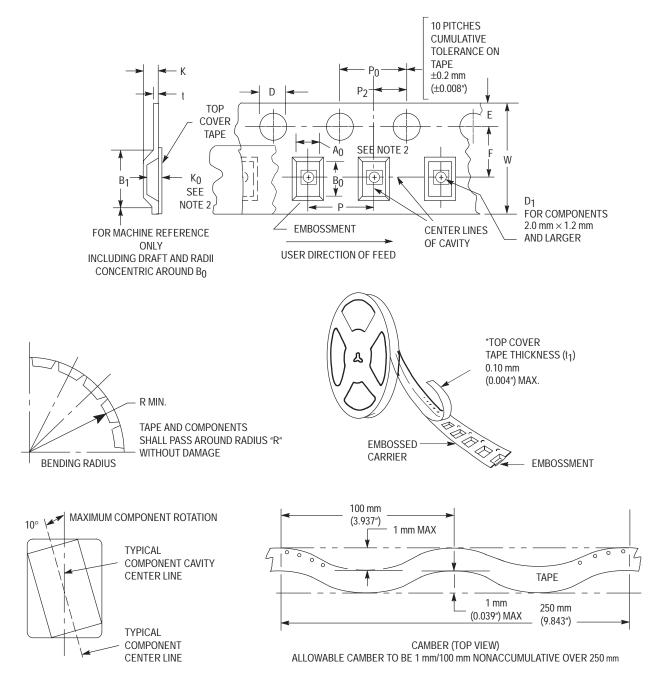
NOTES: DIBENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MM.

CONTROLLING DIMENSION. MM.									
	INC	HES	MILLIN	IETERS					
DIM	MIN	MAX	MIN	MAX					
Α	0.071	0.087	1.80	2.20					
В	0.045	0.053	1.15	1.35					
С	0.031	0.043	0.80	1.10					
D	0.004	0.012	0.10	0.30					
G	0.026	BSC	0.65 BSC						
Н		0.004		0.10					
J	0.004	0.010	0.10	0.25					
К	0.004	0.012	0.10	0.30					
Ν	0.008 REF		0.20	REF					
S	0.079	0.087	2.00	2.20					
V	0.012	0.016	0.30	0.40					











Tape B ₁	D	D1	Е	F	к	Р	Po	P ₂	R	т	w
Size Max 8 mm 4.35 m (0.171)	n 1.5 +0.1/	1.0 mm Min (0.039″)	1.75 ±0.1 mm (0.069 ±0.004")	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004″)	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98″)	0.3 ±0.05 mm (0.01 +0.0038/	8.0 ±0.3 mm (0.315 ±0.012")

EMBOSSED CARR	RIFR DIMENSIONS	(See N	lotes 1	and 2)
			10100 1	

1. Metric Dimensions Govern-English are in parentheses for reference only.

2. A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

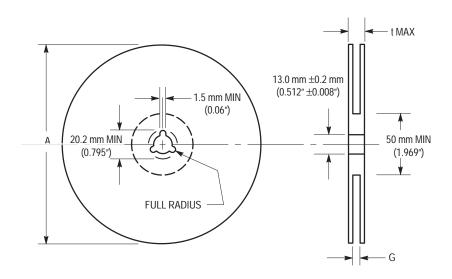
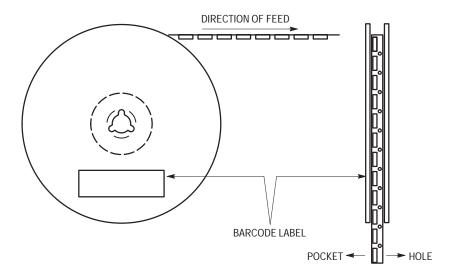


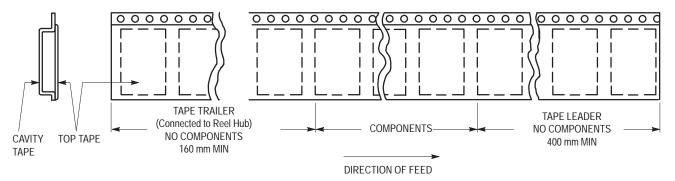
Figure 5. Reel Dimensions

REEL DIMENSIONS

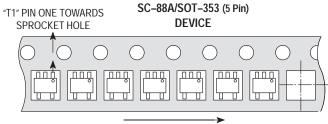
Tape Size	A Max	G	t Max
8 mm	330 mm	8.400 mm, +1.5 mm, -0.0	14.4 mm
	(13")	(0.33", +0.059", -0.00)	(0.56″)











User Direction of Feed

Figure 8. Reel Configuration

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